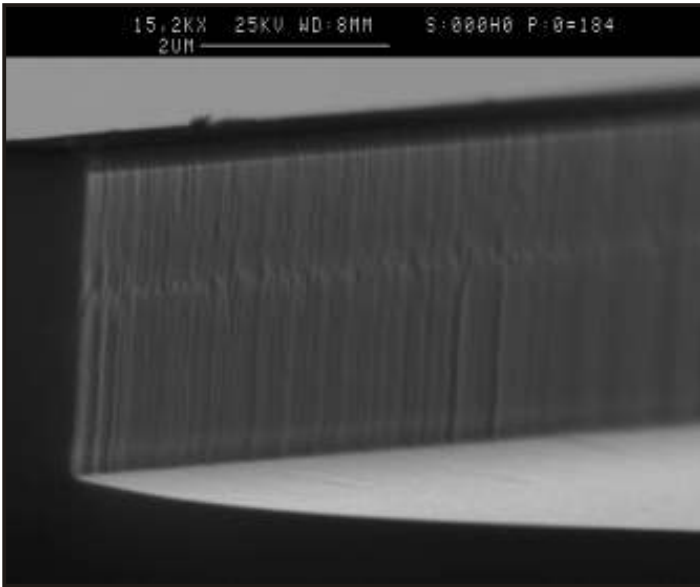


Plasmalab Data

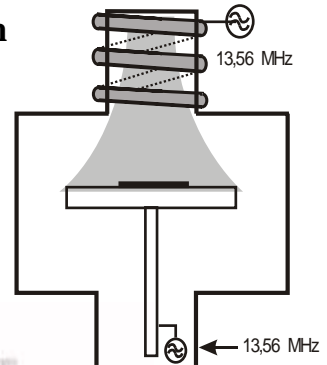
III/ V Heterostructure ICP Etching



InP/InGaAs etch rate 0.9µm/ min
selectivity to SiN 8 : 1



AlGaIn/ GaN etch
GaN etch rate > 0.6 µm/min
Sel to Oxide >7:1
Anisotropic profile
Smooth sidewalls
Clean etch surface



GaP/InGaAlP etch rate > 0.6µm/ min
selectivity to SiO₂ > 8 : 1



Plasmalab System 100